Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSVI)

2SK3569

Switching Regulator Applications

Low drain-source ON-resistance: R_{DS} (ON) = 0.54 Ω (typ.)

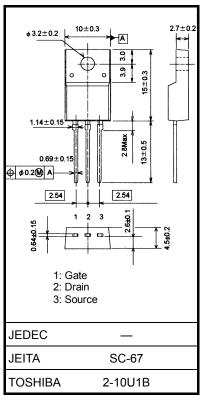
• High forward transfer admittance: |Y_{fS}| = 8.5 S (typ.)

Low leakage current: I_{DSS} = 100 μA (max) (V_{DS} = 600 V)

• Enhancement mode: V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_D = 1 mA)

Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | | Symbol | Rating | Unit |
|--|------------------------------|------------------|------------|------|
| Drain-source voltage | | V_{DSS} | 600 | V |
| Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$) | | V_{DGR} | 600 | V |
| Gate-source voltage | | V_{GSS} | ±30 | V |
| Drain current | DC (Note 1) | I _D | 10 | |
| | Pulse (t = 1 ms) (Note 1) | I _{DP} | 40 | Α |
| Drain power dissipation (Tc = 25°C) | | P _D | 45 | W |
| Single pulse avalanche energy (Note 2) | | E _{AS} | 363 | mJ |
| Avalanche current | | I _{AR} | 10 | Α |
| Repetitive avalanche energy (Note 3) | | E _{AR} | 4.5 | mJ |
| Channel temperature | | T _{ch} | 150 | °C |
| Storage temperature range | | T _{stg} | -55 to 150 | °C |

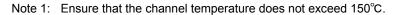


Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

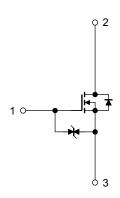
| Characteristics | Symbol | Max | Unit |
|--|------------------------|------|------|
| Thermal resistance, channel to case | R _{th (ch-c)} | 2.78 | °C/W |
| Thermal resistance, channel to ambient | R _{th (ch-a)} | 62.5 | °C/W |



Note 2:
$$V_{DD} = 90~V,~T_{ch} = 25^{\circ}C$$
 (initial), L = 6.36 mH, I_{AR} = 10 A, R_G = 25 Ω

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.



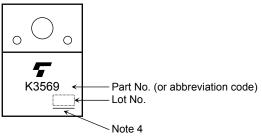
Electrical Characteristics (Ta = 25°C)

| Char | acteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------------|----------------------|---|-----|------|------|------|
| Gate leakage current | | I _{GSS} | $V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±10 | μΑ |
| Gate-source breakdown voltage | | V (BR) GSS | $I_G = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$ | ±30 | _ | | ٧ |
| Drain cut-off current | | I _{DSS} | V _{DS} = 600 V, V _{GS} = 0 V | _ | _ | 100 | μА |
| Drain-source breakdown voltage | | V (BR) DSS | I _D = 10 mA, V _{GS} = 0 V | 600 | _ | | ٧ |
| Gate threshold ve | oltage | V _{th} | V _{DS} = 10 V, I _D = 1 mA | 2.0 | _ | 4.0 | ٧ |
| Drain-source ON | -resistance | R _{DS} (ON) | V _{GS} = 10 V, I _D = 5 A | _ | 0.54 | 0.75 | Ω |
| Forward transfer | admittance | Y _{fs} | V _{DS} = 10 V, I _D = 5 A | 2.4 | 8.5 | _ | S |
| Input capacitance | pacitance C _{iss} | | | _ | 1500 | _ | |
| Reverse transfer capacitance | | C _{rss} | $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | _ | 15 | | pF |
| Output capacitance | | Coss | | _ | 180 | _ | |
| Switching time | Rise time | t _r | $\begin{array}{c c} 10 \text{ V} & \text{ID} = 5 \text{ A} & \text{Vout} \\ \hline VGS & \\ 0 \text{ V} & \\ \hline SO \Omega & \\ \end{array} \begin{array}{c} R_L = \\ 40 \Omega \\ \end{array}$ $V_{DD} \approx 200 \text{ V}$ | _ | 22 | _ | |
| | Turn-on time | t _{on} | | _ | 50 | _ | |
| | Fall time | t _f | | _ | 36 | _ | ns |
| | Turn-off time | t _{off} | Duty \leq 1%, $t_W = 10 \mu s$ | _ | 180 | _ | |
| Total gate charge | | Qg | | _ | 42 | _ | |
| Gate-source charge | | Q _{gs} | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$ | _ | 23 | _ | nC |
| Gate-drain charge | | Q _{gd} | | _ | 19 | | |

Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|------|------|
| Continuous drain reverse current (Note 1) | I _{DR} | _ | _ | _ | 10 | Α |
| Pulse drain reverse current (Note 1) | I _{DRP} | _ | _ | _ | 40 | Α |
| Forward voltage (diode) | V _{DSF} | I _{DR} = 10 A, V _{GS} = 0 V | _ | _ | -1.7 | ٧ |
| Reverse recovery time | t _{rr} | $I_{DR} = 10 \text{ A}, V_{GS} = 0 \text{ V},$ | | 1300 | | ns |
| Reverse recovery charge | Q _{rr} | dI _{DR} /dt = 100 A/μs | | 16 | | μС |

Marking

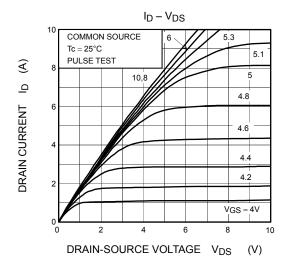


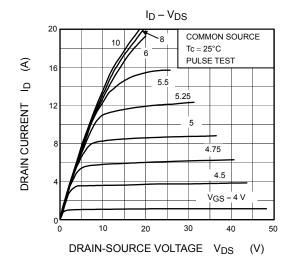
Note 4: A line under a Lot No. identifies the indication of product Labels.

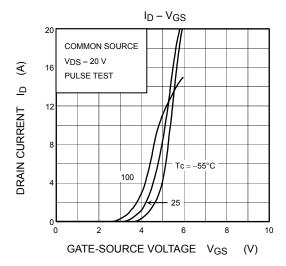
Not underlined: [[Pb]]/INCLUDES > MCV

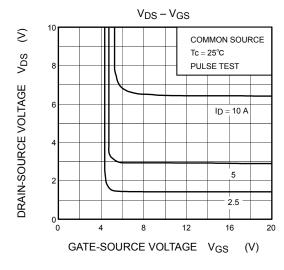
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

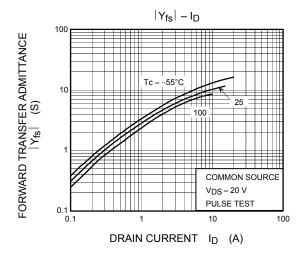
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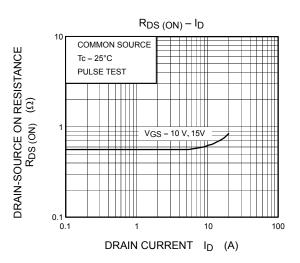




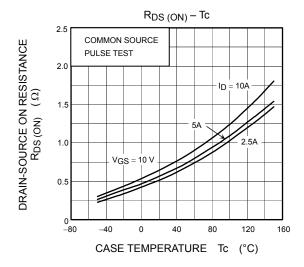


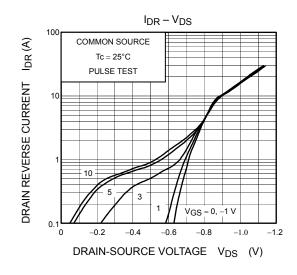


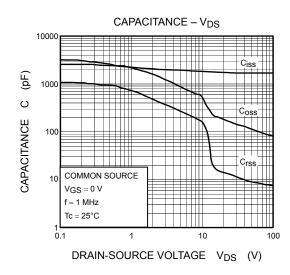


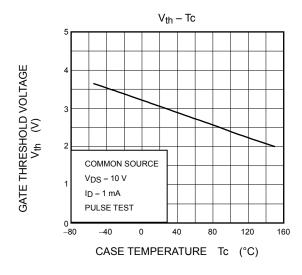


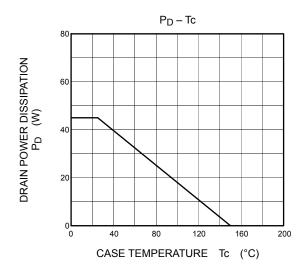
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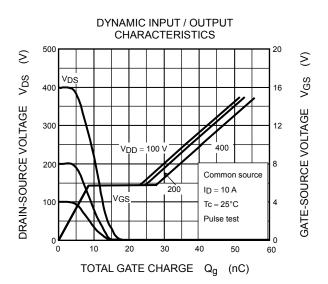


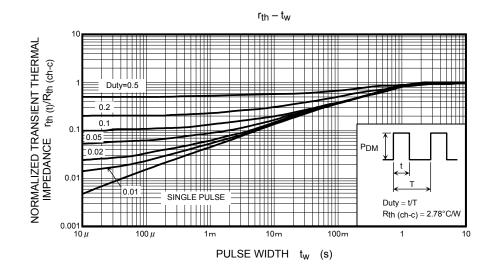


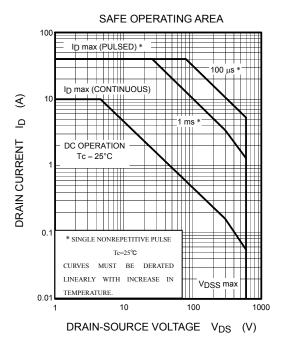


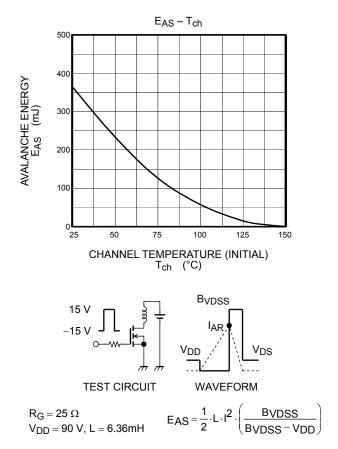












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